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Hyperfast Rectifier, 2 x 3 A FRED Pt[®]

FlatPAK 5 x 6

1, 2 • 7, 8 3. 4 • 5. 6

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 3 A					
V _R	200 V					
V _F at I _F	0.71 V					
t _{rr}	25 ns					
T _J max.	175 °C					
Package	FlatPAK 5 x 6					
Circuit configuration	Separated cathode					

FEATURES

- Hyper fast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002, meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200				
Average rectified forward current pe	per device	I _{F(AV)}	T _{Solderpad} = 170 °C, DC	3	V			
Average rectilied forward current pe	er device		$T_{Solderpad} = 169 \ ^{\circ}C, D = 0.5$	3				
Non-repetitive peak surge current	repetitive peak surge current per device		T_J = 25 °C, 10 ms sinusoidal pulse	147	Δ			
peak surge current	er diode	IFSM		70	A			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. U								
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-			
Forward voltage	V _F	I _F = 3 A	-	0.88	0.94	V		
Forward voltage		I _F = 3 A, T _J = 150 °C	-	0.71	0.74			
Reverse leakage current	I _R	$V_{R} = V_{R}$ rated	-	-	2	μA		
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	6	40			
Junction capacitance	CT	V _R = 200 V	-	14	-	pF		

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FREE



DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	0 A/µs, V _R = 30 V	-	26	-			
Povereo recovery time	t _{rr}	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25			
Reverse recovery time		T _J = 25 °C		-	15	-	ns		
		T _J = 125 °C	I _F = 3 A dI _F /dt = 200 A/μs V _B = 160 V	-	25	-			
Deals receivers everyont		T _J = 25 °C		-	2	-	٨		
Peak recovery current	IRRM	T _J = 125 °C		-	3	-	A		
	0	T _J = 25 °C		-	12	-	nC		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	40	-	no		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾⁽²⁾		-	90	103				
Thermal resistance, junction to mount	R _{thJM} ⁽³⁾		-	2.3	2.6	°C/W			

Notes

 $^{(1)}$ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1 \times R_{thJA}$

 $^{(2)}$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

⁽³⁾ Mounted on infinite heatsink

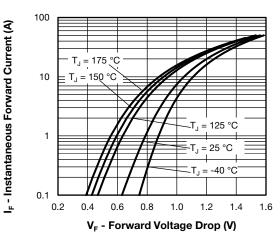


Fig. 1 - Typical Forward Voltage Drop Characteristics

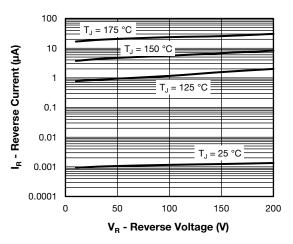


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



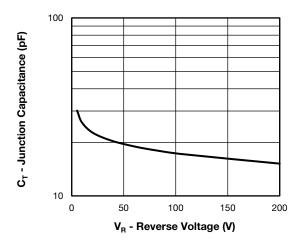


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

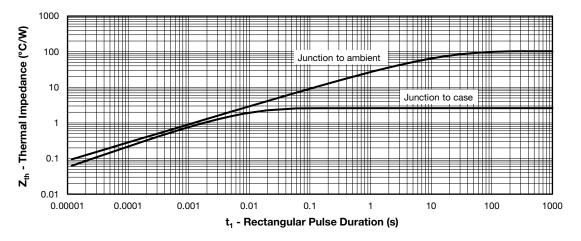
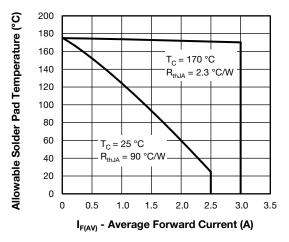
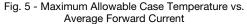


Fig. 4 - Maximum Thermal Impedance Z_{th} Characteristics

Average Power Loss (W)



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Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see Fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

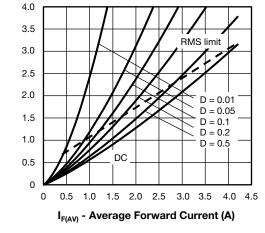


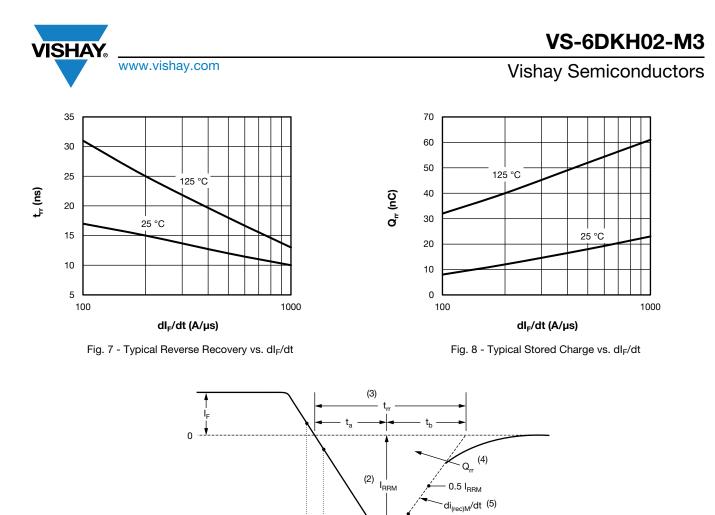
Fig. 6 - Forward Power Loss Characteristics

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(1) di_F/dt (1) di_E/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

0.75 I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(3) t_{rr} - reverse recovery time measured (5) di_{(rec)M}/dt - peak rate of change of from zero crossing point of negative current during t_b portion of t_{rr} going I_F to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

Fig. 9 - Reverse Recovery Waveform and Definitions

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SHAY

Device code	VS-	6	D	к	н	02	-M3
	•••	Ŭ	Ľ		••	02	
	1	2	3	4	5	6	7
	1	- Visl	nay Sen	niconduo	ctors pro	oduct	
	2	- Cur	rent rati	ng (6 =	6 A)		
	3	- Circ	uit conf	iguratior	ו:		
		D =	separat	ted cath	ode		
	4	- K=	FlatPA	K packa	ge		
	5	- Pro	cess typ	e:			
		H =	hyperfa	st recov	very		
	6	- Volt	age coo	de (02 =	200 V)		
	7	M3	= halog	gen-free	, RoHS	complia	ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	UNIT WEIGHT (g)	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-6DKH02-M3/H	0.10	н	1500	7"diameter plastic tape and reel			
VS-6DKH02-M3/I	0.10	I	6000	13"diameter plastic tape and reel			

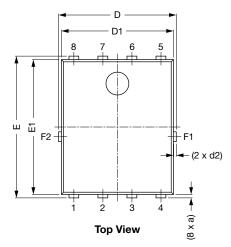
LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?96056						
Part marking information	www.vishay.com/doc?96059					
Packaging information	www.vishay.com/doc?88869					
SPICE model	www.vishay.com/doc?96882					

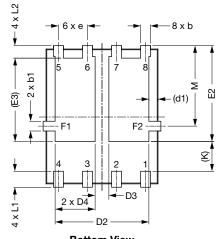




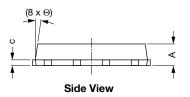
FlatPAK 5 x 6 (Dual)

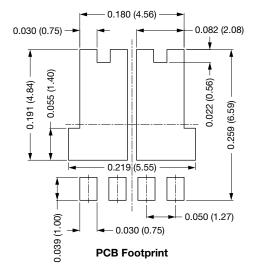
DIMENSIONS in inches (millimeters)











DIM		INCHES		MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.035	0.039	0.043	0.89	0.99	1.09	
(a)	-	0.006	-	-	0.15	-	
b	0.013	0.017	0.020	0.32	0.43	0.52	
b1	0.013	0.017	0.020	0.32	0.43	0.52	
С	0.008	-	0.014	0.20	-	0.35	
D	0.197	0.203	0.209	5.00	5.15	5.30	
D1	0.189	0.193	0.197	4.80	4.90	5.00	
D2	0.154	0.161	0.169	3.90	4.10	4.30	
D3	0.020	0.024	0.031	0.50	0.60	0.80	
D4	0.063	0.069	0.075	1.60	1.75	1.90	
(d1)	-	0.016	-	-	0.40	-	
(d2)	-	0.005	-	-	0.125	-	
E	0.238	0.244	0.250	6.05	6.20	6.35	

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Outline Dimensions



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DIM.		INCHES		MILLIMETERS				
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
E1	0.228	0.232	0.236	5.80	5.90	6.00		
E2	0.157	0.165	0.173	4.00	4.20	4.40		
(E3)	-	0.144	-	-	3.65	-		
е		0.050 BSC		1.27 BSC				
(K)	0.039	-	-	1.00	-	-		
L1	0.019	-	0.043	0.48	-	1.10		
L2	0.012	-	0.031	0.30	-	0.80		
М	0.128	0.138	0.148	3.25	3.50	3.75		
Θ	0°	-	10°	0°	-	10°		

Notes

٠ Dimensioning and tolerancing per ASME Y14.5-2009

Dimensions D1 and E1 do not include mold flash or gate burrs ٠

Dimension (XX) means reference only ٠



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